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PATENT & TRADEMARK OFFICE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	DAI et al.	Examiner:	Unknown
Serial No.:	10/679,936	Group Art Unit:	2811
Filed:	October 6, 2003	Docket No.:	STFD.041PA (S02-214)
Title:	CARBON NANOTUBE CIRCUITS WITH HIGH-κ DIELECTRICS		

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence and the papers, as described hereinabove, are being deposited in the United States Postal Service, as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on March 11, 2004.

By: Kelly J. Ledin

INFORMATION DISCLOSURE STATEMENT (37 C.F.R. §1.97(b))

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

With regard to the above-identified application, this statement should be considered because it is submitted either within three months of the filing date or before the first Office Action of the above-identified application.

Applicant would like to bring to the attention of the Examiner the following references, which were mentioned in the underlying provisional application:

1. Wilk, G. D., Wallace, R. M. & Anthony, J. M. High-k gate dielectrics: current status and materials properties considerations. *J. Appl. Phys.* **89**, 5243-5275 (2001).

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No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§ 102 and 103 and Applicants reserve the right, pursuant to 37 C.F.R. § 1.131 or otherwise, to establish that the reference(s) are not "prior art." Moreover, Applicants do not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended.

Respectfully submitted,

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Date: March 11, 2004

By: _____
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